L Number	Hits	Search Text	DB	Time stamp
31	40	lateral near4 zener adj diode	USPAT;	2002/03/07 10:23
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
32	51	(lateral or horizontal) near4 zener adj	USPAT;	2002/03/07 10:23
	-	diode	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	446	("257/339").CCLS.	USPAT;	2002/03/06 15:19
		(20.,000 , .0020.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	1004	(#252/255#) CCI C	IBM TDB USPAT;	2002/03/02 21:29
-	1004	("257/355").CCLS.	US-PGPUB;	2002/03/02 21.29
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	1672		USPAT;	2002/03/02 21:29
		or (("257/355").CCLS.)	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	1474		USPAT;	2002/03/02 21:31
		(("257/339").CCLS.) or (("257/355").CCLS.)) and (@pd<20000606 or	US-PGPUB; EPO; JPO;	
		((~257/355).CCLS.)) and (@pd<2000000 of	DERWENT;	
			IBM TDB	
-	21143	npn same pnp	USPAT;	2002/03/02 21:31
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
-	114		USPAT;	2002/03/02 21:31
		(("257/339").CCLS.) or	US-PGPUB;	
		(("257/355").CCLS.)) and (@pd<20000606 or @rlad<20010609)) and (npn same pnp)	EPO; JPO; DERWENT;	
		errad<20010003// and (hph same php)	IBM TDB	
_	322	protection adj circuit.ti,ab. and vss	USPAT;	2002/03/03 12:40
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	2	protection adj circuit.ti,ab. and vss adj	USPAT;	2002/03/03 12:41
	_	power adj line and p+ and n+	US-PGPUB;	
			EPO; JPO;	
		·	DERWENT; IBM TDB	
_	314	("257/173").CCLS.	USPAT;	2002/03/03 12:45
		,	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	314	("257/173").CCLS.	IBM TDB USPAT;	2002/03/03 12:46
	214	(257,175 7.0000.	US-PGPUB;	2502,05,05 12.40
			EPO; JPO;	
			DERWENT;	
. _	197	("257/173").CCLS.	IBM TDB USPAT	2002/03/03 13:33
_	23		USPAT;	2002/03/03 13:33
		,	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	282	("257/339").CCLS.	IBM TDB USPAT	2002/03/03 13:34
	202	1 (207/30) 7.0000.	JULKI	1 2002/03/03 13:34

				0000/00/00
-	280	(("257/339").CCLS.) not	USPAT;	2002/03/03 13:46
		(("257/173").CCLS.)	US-PGPUB;	
			EPO; JPO;	
	'		DERWENT;	
	200	//#257/220#\ CCTC \ mot	IBM TDB USPAT	2002/03/03 14:01
-	280	(("257/339").CCLS.) not	USPAT	2002/03/03 14:01
	501	(("257/173").CCLS.)	HCDAM	2002/02/03 15-22
-	501	(257/355.ccls. not 257/173.ccls.) not	USPAT	2002/03/03 15:22
	37	257/339.ccls. (vertical near2 (npn or pnp) near2	HCDAM.	2002/03/03 17:16
-	31	transistor) same protect\$3 same (surge or	USPAT; US-PGPUB;	2002/03/03 17.10
		esd or electrostatic adj discharge or	EPO; JPO;	
		human adj body adj model or hbm or	DERWENT;	
1		breakdown adj voltage)	IBM TDB	
_	76		USPAT;	2002/03/03 17:16
	'`	protection	US-PGPUB;	2002,03,03 1
		proceeding	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	15	zener adj diode and mosfet and esd adj	USPAT;	2002/03/03 17:17
		protection and vss	US-PGPUB;	
		•	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	4	zener adj diode and (mos or mosfet).ti,ab.	USPAT;	2002/03/03 18:02
		and esd adj protection and vss	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	4	zener adj diode and (mos or mosfet or	USPAT;	2002/03/03 19:37
		nmosfet or nmos or pmos or pmosfet or	US-PGPUB;	
		field adj effect adj transistor).ti,ab.	EPO; JPO;	
		and (electrostatic adj discharge or esd)	DERWENT;	
		adj protection.ti,ab. and vss	IBM TDB	
-	2		USPAT	2002/03/03 19:38
-	0	("prevent adj latch-up.ti,ab.").PN.	USPAT;	2002/03/03 20:18
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	460		IBM TDB	2002/02/02 20:10
-	462	prevent adj latch-up.ti,ab.	USPAT;	2002/03/03 20:19
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	44	prevent adj latch-up.ti,ab.	USPAT	2002/03/03 20:19
_	13	integrated adj circuit.ti,ab. and (prevent	USPAT	2002/03/03 20:19
		adj latch-up).ti,ab.		
-	О	09/866,782.ap.	USPAT;	2002/03/05 20:29
1		, , , , , , , , , , , , , , , , , , ,	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	0	"08-101176"	JPO	2002/03/05 20:36
-	17	dairitsu	JPO	2002/03/05 20:36
-	25	dairitsu	JPO;	2002/03/05 20:37
			DERWENT	
-	317	("257/173").CCLS.	USPAT;	2002/03/05 21:38
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
]			IBM TDB	
-	446	("257/339").CCLS.	USPAT;	2002/03/05 21:38
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	

_	1005	("257/355").CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/03/05 21:38
_	1675	(("257/173").CCLS.) or (("257/339").CCLS.) or (("257/355").CCLS.)	IBM TDB USPAT; US-PGPUB;	2002/03/05 21:40
		02 ((201, 000 , 100201,	EPO; JPO; DERWENT; IBM TDB	
-	2	((("257/173").CCLS.) or (("257/339").CCLS.) or (("257/355").CCLS.)) and silicide and (esd or electrostatic adj discharge or hbm or	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/03/05 21:44
		human adj body adj model or surge).ti,ab. and (mos or nmos or pmos or dmos or ldmos or mosfet or nmosfet or pmosfet or dmosfet	IBM TDB	
-	3		USPAT;	2002/03/05 21:56
		(("257/339").CCLS.) or (("257/355").CCLS.)) and silicide and (esd or electrostatic adj discharge or hbm or human adj body adj model or surge or	US-PGPUB; EPO; JPO; DERWENT; IBM TDB	
		protection).ti,ab. and (mos or nmos or pmos or dmos or ldmos or mosfet or nmosfet or pmosfet or dmosfet or ldmosfet).ti,ab. and zener and bipolar adj transistor		
-	6	((("257/173").CCLS.) or (("257/339").CCLS.) or (("257/355").CCLS.)) and silicide and (esd or electrostatic adj discharge or hbm or human adj body adj model or surge or protection).ti,ab. and (mos or nmos or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/05 22:00
		pmos or dmos or ldmos or mosfet or nmosfet or pmosfet or dmosfet or ldmosfet).ti,ab. and zener		0000/00/05 00 00
_	36	<pre>((("257/173").CCLS.) or (("257/339").CCLS.) or (("257/355").CCLS.)) and (esd or electrostatic adj discharge or hbm or human adj body adj model or surge or protection).ti,ab. and (mos or nmos or pmos or dmos or ldmos or mosfet or nmosfet or pmosfet or dmosfet or ldmosfet).ti,ab. and zener</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/05 22:00
-	0	(MOS or MOSFET) near12 protect\$3 near12 (each adj other)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/03/06 08:44
_	28	plurality adj2 (mos or mosfet) and (esd or electrostatic adj discharge) adj protect\$3	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/03/06 08:55
-	0	mosfet adj array and esd adj protection.ti,ab.	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/03/06 08:56
-	4	mosfet adj array and esd adj protection	IBM TDB USPAT; US-PGPUB;	2002/03/06 14:00
_	2466	phosphor\$3 near6 dopant near6 type	EPO; JPO; DERWENT; IBM TDB USPAT;	2002/03/06 14:16
			US-PGPUB; EPO; JPO; DERWENT; IBM TDB	
				— · -

-	4	Schottky adj diode same silicide adj2	USPAT;	2002/03/06 14:19
		(layer or film) same protect\$3	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	0	 Schottky adj diode same silicide adj2	IBM TDB USPAT;	2002/03/06 14:19
_		(layer or film) same esd adj protect\$3	US-PGPUB;	2002/03/06 14:19
		(layer of film) same esd adj proceccas	EPO; JPO;	
İ			DERWENT;	
			IBM TDB	
_	19	Schottky adj diode same esd adj protect\$3	USPAT;	2002/03/06 14:46
1	1	benevery day arous bame oba day proceeds	US-PGPUB;	2002,00,00 21110
		·	EPO; JPO;	
	1		DERWENT;	
			IBM TDB	
-	4		USPAT;	2002/03/06 14:56
		same decreas\$3 same schottky	US-PGPUB;	
ĺ			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	54	,	USPAT;	2002/03/06 14:58
		circuit	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	2	schottky adj diode same protection adj2	USPAT;	2002/03/06 14:58
		circuit same silicide	US-PGPUB;	2002/03/00 14:50
		Circuit Same Silicide	EPO; JPO;	
	1		DERWENT;	
			IBM TDB	
-	50	(schottky adj diode same (silicide adj	USPAT;	2002/03/06 15:25
		(layer or film) or salicide)) and (esd or	US-PGPUB;	
		electrostatic adj discharge or protect\$3	EPO; JPO;	
		or hbm or human adj body adj model or	DERWENT;	
		surge)	IBM TDB	
-	4	(schottky adj diode near12 (silicide adj	USPAT;	2002/03/06 15:47
	,	(layer or film) or salicide)) and (esd or	US-PGPUB;	
		electrostatic adj discharge or protect\$3	EPO; JPO;	
		or hbm or human adj body adj model or	DERWENT;	
	3	surge).ti,ab.	IBM TDB	2002/02/06 15:50
-	3	5166089.pn.	USPAT; US-PGPUB;	2002/03/06 15:50
1			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	jp-406224376\$-\$.did.	USPAT;	2002/03/06 15:50
		2.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
- .	2	jp-06224376\$-\$.did.	USPAT;	2002/03/06 16:22
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	60		IBM TDB	2002/02/05 16:02
_	62	amerasekera.in.	USPAT;	2002/03/06 16:22
			US-PGPUB;	
		•	EPO; JPO; DERWENT;	
			IBM TDB	
_	23	amerasekera.in. and bipolar adj transistor	USPAT;	2002/03/06 17:25
	2.5	americani and proper adj cranorotor	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	0	((triple adj well or triple-well) same	USPAT;	2002/03/06 16:46
		bipolar adj transistor) and third adj2	US-PGPUB;	
		diffusion	EPO; JPO;	
			DERWENT;	
L			IBM TDB	

_	33	(triple adj well or triple-well) same bipolar adj transistor	USPAT; US-PGPUB;	2002/03/06 16:47
			EPO; JPO; DERWENT; IBM TDB	
-	30	(triple adj well or triple-well) same bipolar adj transistor and (MOS or NMOS or PMOS or mosfet or pmosfet or nmosfet or	USPAT; US-PGPUB; EPO; JPO;	2002/03/06 16:48
		cmos or cmosfet)	DERWENT; IBM TDB	
-	5	(triple adj well or triple-well) same bipolar adj transistor and (MOS or NMOS or PMOS or mosfet or pmosfet or nmosfet or cmos or cmosfet).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/03/06 16:58
_	6	"5872032"	IBM TDB USPAT; US-PGPUB; EPO; JPO;	2002/03/06 16:53
	2	5072022	DERWENT; IBM TDB	2002/03/06 16:53
_	3	5872032.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/03/06 16:53
-	1	(triple adj well or triple-well) same bipolar adj transistor and (MOS or NMOS or	IBM TDB USPAT; US-PGPUB;	2002/03/06 17:00
		PMOS or mosfet or pmosfet or nmosfet or cmos or cmosfet).ti,ab. and protect\$3	EPO; JPO; DERWENT; IBM TDB	
_	1	(protect\$3 same (triple adj well or triple-well) same bipolar adj transistor) and (MOS or NMOS or PMOS or mosfet or pmosfet or nmosfet or cmos or cmosfet)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/03/06 17:04
	52	protect\$3 and ((third near2 (impurity or diffusion)) same bipolar adj transistor) and (MOS or NMOS or PMOS or mosfet or	IBM TDB USPAT; US-PGPUB; EPO; JPO;	2002/03/06 17:06
_	12	<pre>pmosfet or nmosfet or cmos or cmosfet) protect\$3.ti,ab. and ((third near2 (impurity or diffusion)) same bipolar adj</pre>	DERWENT; IBM TDB USPAT; US-PGPUB;	2002/03/06 17:07
;		transistor) and (MOS or NMOS or PMOS or mosfet or pmosfet or nmosfet or cmos or cmosfet).ti,ab.	EPO; JPO; DERWENT; IBM TDB	
_	317	("257/173").CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/03/06 17:48
-	760	(zener adj diode nearl2 (source or drain)) and (electrostatic adj discharge or surge or esd)	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/03/07 07:57
_	196	(zener adj diode nearl2 (source or drain)) and (electrostatic adj discharge or surge or esd).ti,ab.	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/03/07 07:58
_	157	(zener adj diode near6 (source or drain)) and (electrostatic adj discharge or surge or esd).ti,ab.	IBM TDB USPAT; US-PGPUB; EPO; JPO;	2002/03/07 08:02
_	12	(zener adj diode near6 (source or drain))	DERWENT; IBM TDB USPAT;	2002/03/07 08:09
		and (electrostatic adj discharge or surge or esd) and (mos or mosfet or nmos or nmosfet or pmos or pmosfet or dmos or dmosfet or ldmos or ldmosfet) and	US-PGPUB; EPO; JPO; DERWENT; IBM TDB	
		(silicide or salicide)		1

r			1	0000 (00 (00 00 00
-	0	(lateral adj zener adj diode near6 (source		2002/03/07 08:09
		or drain)) and silicide	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	0	(lateral adj zener adj diode near6 (source	1	2002/03/07 08:10
[or drain))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	13	lateral adj zener adj diode	USPAT;	2002/03/07 10:18
İ			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
} <u> </u>	0	57190357.URPN.	USPAT:	2002/03/07 09:23
	_		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	57190357.URPN.	1	2002/03/07 09:23
	_		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	57190357.URPN.	USPAT;	2002/03/07 09:23
			US-PGPUB;	,,,
			EPO; JPO;	ł
			DERWENT;	-
			IBM TDB	
_	1	"5023521".PN.	USPAT	2002/03/07 09:24